

**General Features**

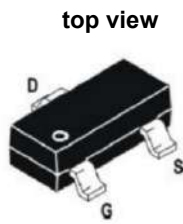
- $R_{DS(ON)} < 21m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)} < 28m\Omega$ @ $V_{GS} = -2.5V$
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package

Product Summary

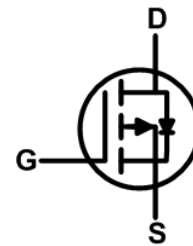
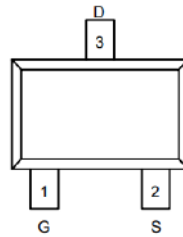
VDS	-20	V
$R_{DS(on),max.}@ V_{GS}=4.5 V$	21	m Ω
ID	-9	A

Applications

- PWM Applications
- Load Switch
- Power Management



SOT23-3



P-channel

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	-9
		$T_C = 100^\circ C$	-5
I_{DM}	Pulsed Drain Current ^{note1}	-15	A
P_D	Power Dissipation	$T_C = 25^\circ C$	1.8
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$

**Electrical Characteristics** ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-20V, V_{GS}=0V,$	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.7	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=-4.5V, I_D=-4A$	-	16	21	m Ω
		$V_{GS}=-2.5V, I_D=-3A$	-	20	28	
g_{FS}	Forward Transconductance	$V_{DS}=-5V, I_D=-6.7A$	20	-	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-10V, V_{GS}=0V,$ $f=1.0MHz$	-	1200	-	pF
C_{oss}	Output Capacitance		-	230	-	pF
C_{rss}	Reverse Transfer Capacitance		-	90	-	pF
Q_g	Total Gate Charge	$V_{DS}=-16V, I_D=-9A,$ $V_{GS}=-4.5V$	-	15	48	nC
Q_{gs}	Gate-Source Charge		-	4	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-10V, I_D=-1A,$ $R_{GEN}=10\Omega, V_{GS}=-4.5V$	-	11	-	ns
t_r	Turn-on Rise Time		-	18	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	30	-	ns
t_f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-1	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-10	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=-8A$	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$



■ Typical Performance Characteristics

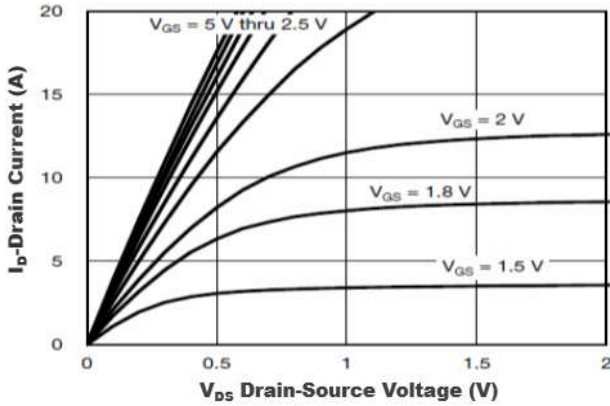


Figure1. Output Characteristics

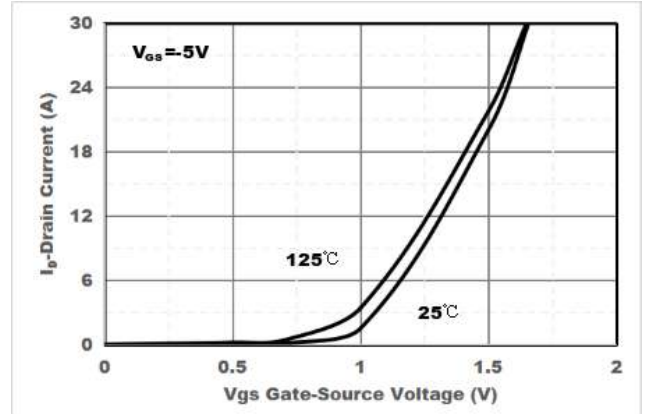


Figure2. Transfer Characteristics

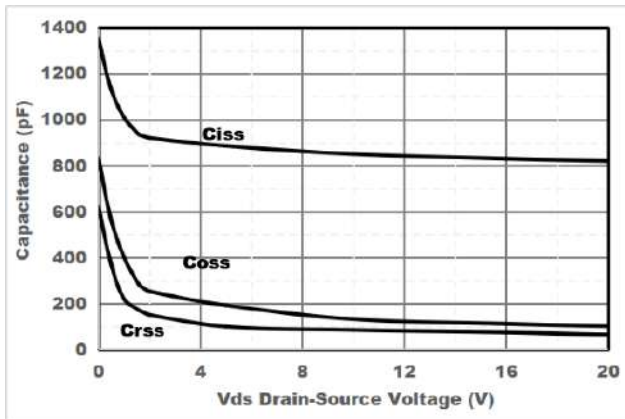


Figure3. Capacitance Characteristics

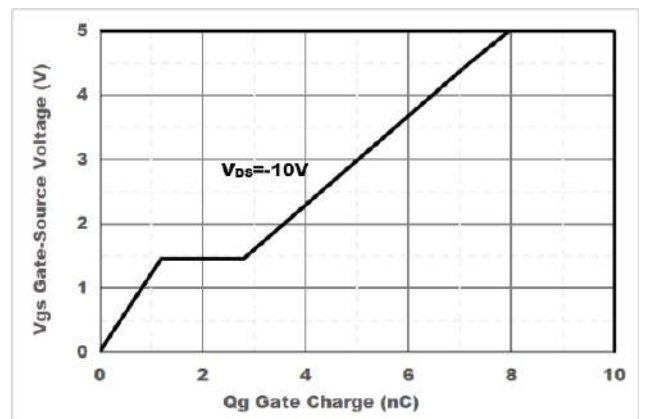


Figure4. Gate Charge

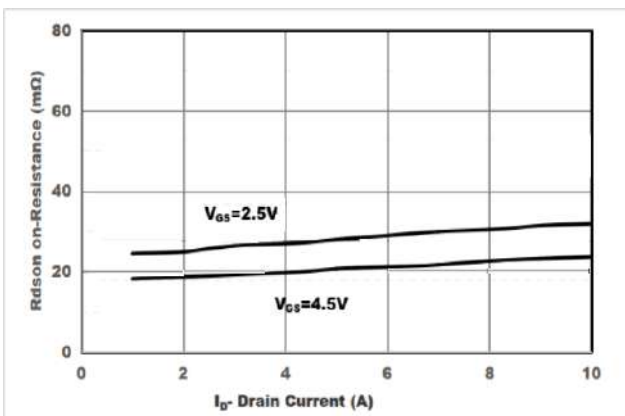


Figure5. Drain-Source on Resistance

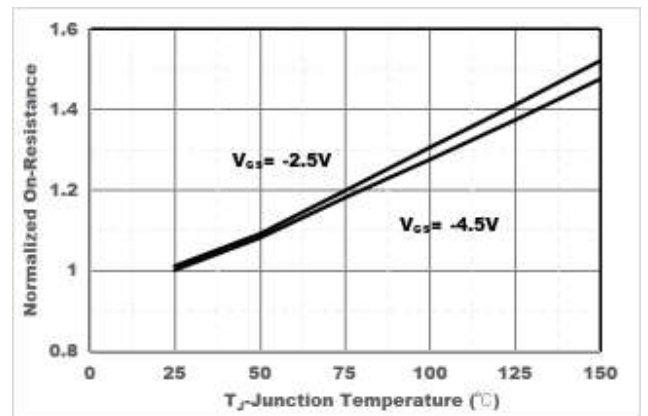


Figure6. Drain-Source on Resistance

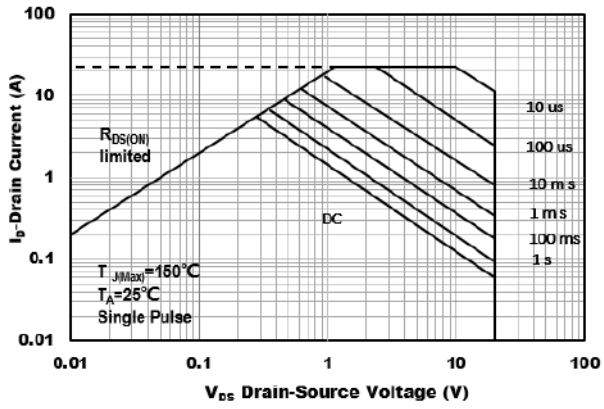


Figure7. Safe Operation Area

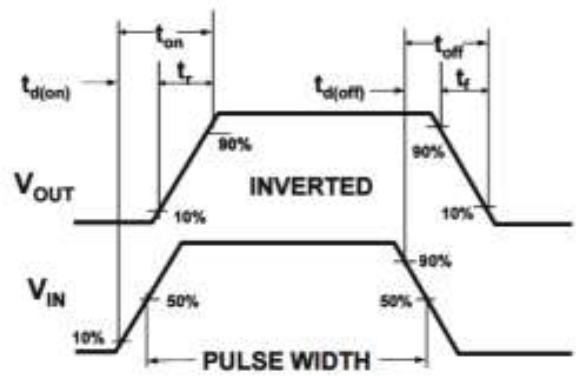
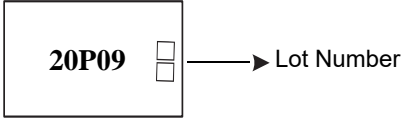


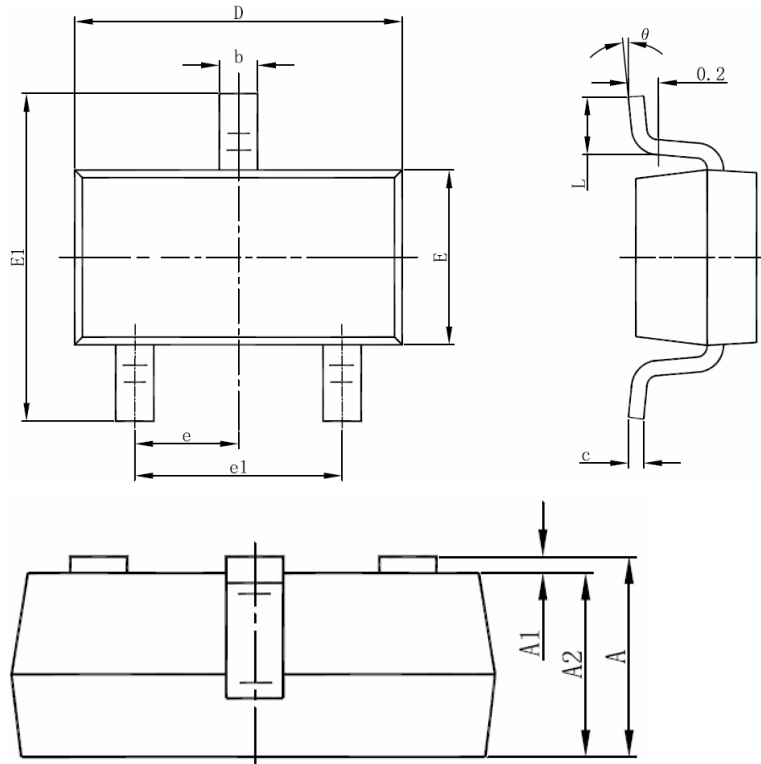
Figure8. Switching wave

Ordering and Marking Information

Ordering Device No	Marking	Package	Packing	Quantity
ASDM20P09ZB-R	20P09	SOT23-3	Tape&Reel	3000/Reel

PACKAGE	MARKING
SOT23-3	 <p>The marking diagram shows a rectangular box containing the text '20P09' followed by two small vertical rectangles. An arrow points from these two rectangles to the text 'Lot Number'.</p>

SOT-23-3L PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

**IMPORTANT NOTICE**

Xi'an Ascend Semiconductor incorporated MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Xi'an Ascend Semiconductor Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Xi'an Ascend Semiconductor Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Xi'an Ascend Semiconductor Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume .

all risks of such use and will agree to hold Ascendsemi Incorporated and all the companies whose products are represented on Xi'an Ascend Semiconductor Incorporated website, harmless against all damages.

Xi'an Ascend Semiconductor Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Xi'an Ascend Semiconductor Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Xi'an Ascend Semiconductor Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

www.ascendsemi.com